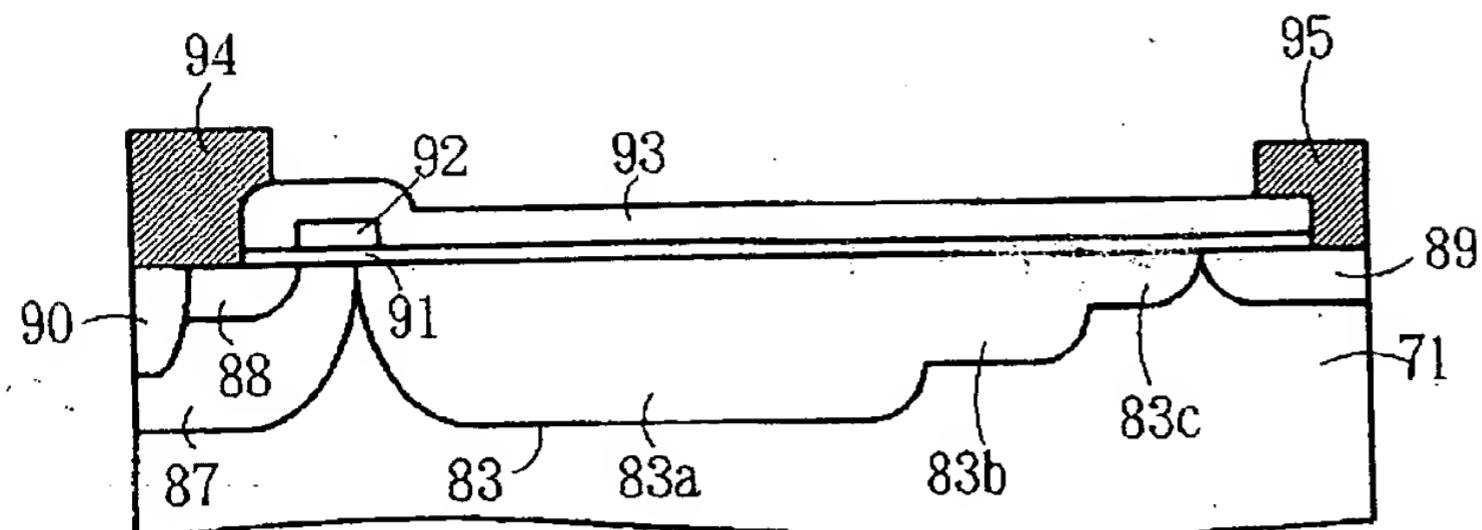


Fig. 1



- | | |
|-------------------------------|---|
| 71: n-type silicon substrate | 89: n-type drain region |
| 83: p-type offset region | 90: p ⁺ -type contact region |
| 83a: First p-type sub-region | 91: Gate insulation film |
| 83b: Second p-type sub-region | 92: Gate electrode |
| 83c: Third p-type sub-region | 93: Insulation film |
| 87: p-type base region | 94: Source electrode |
| 88: n-type source region | 95: Drain electrode |

Fig. 2

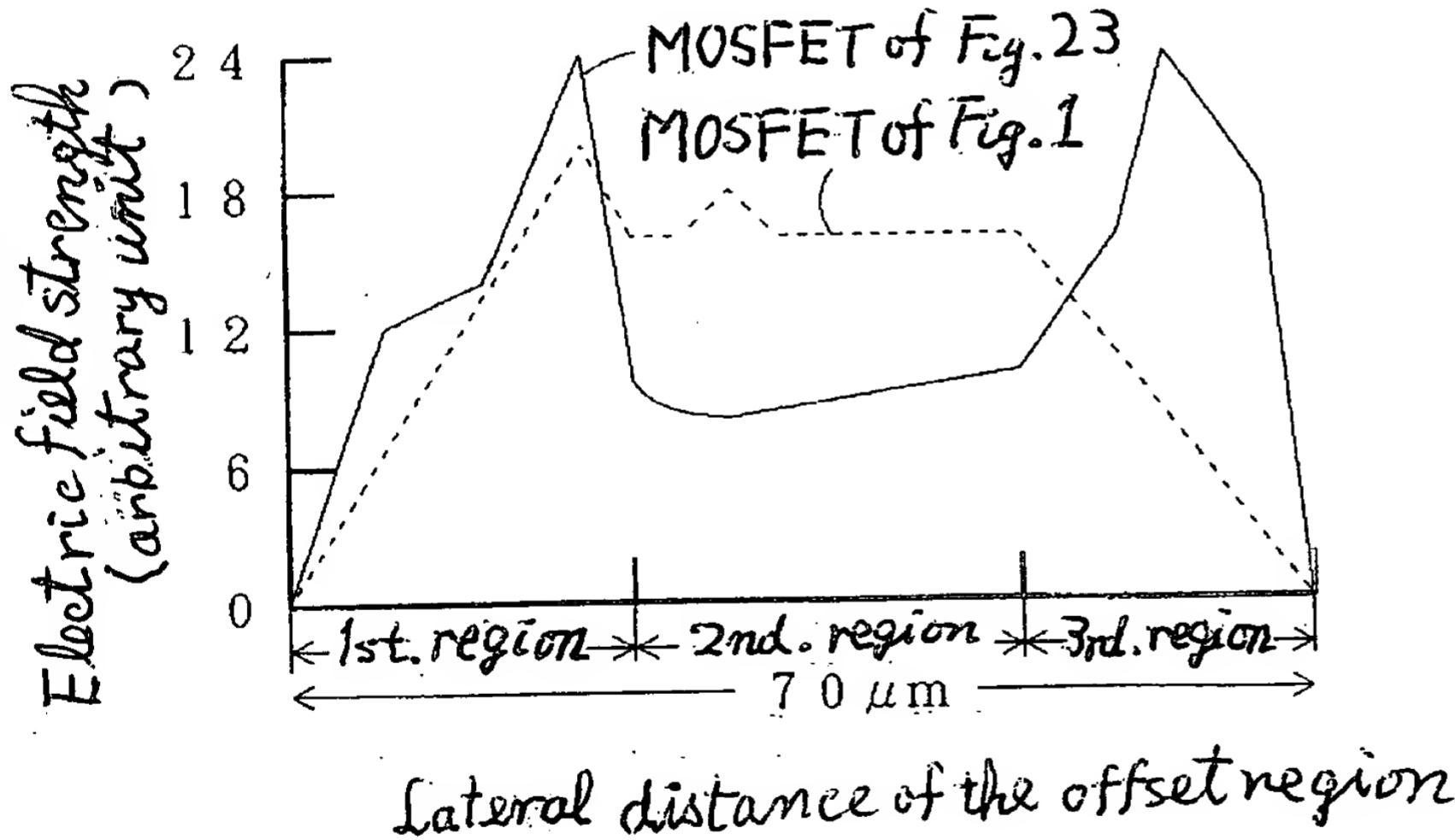


Fig. 3

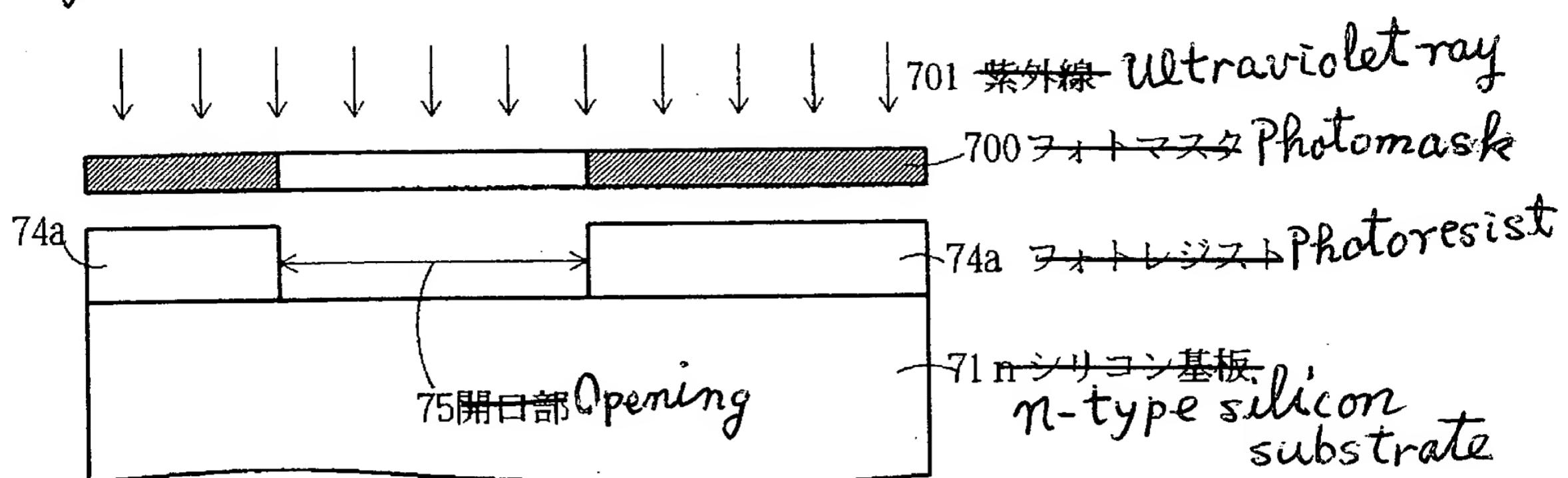


Fig. 4

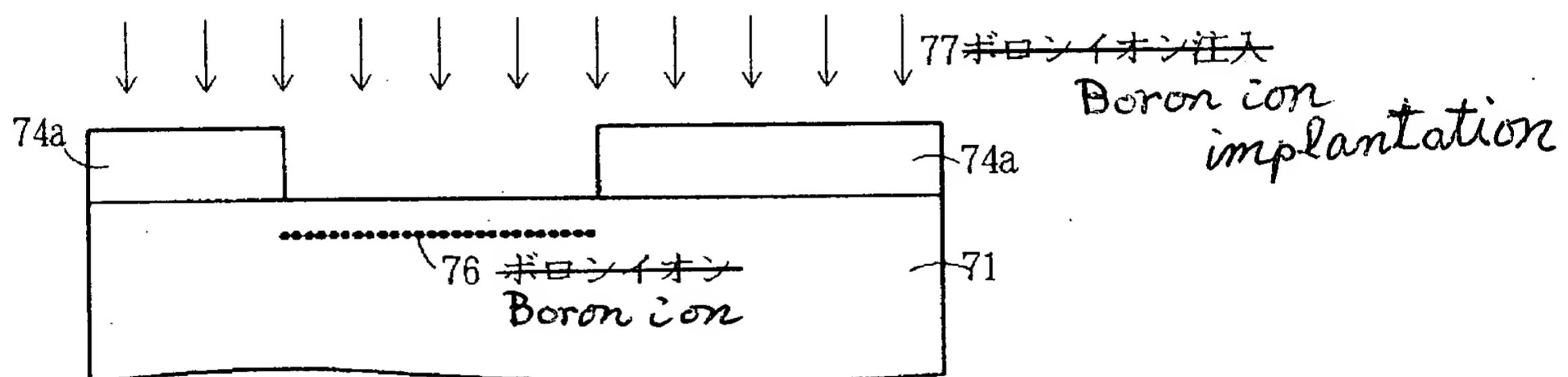


Fig. 5

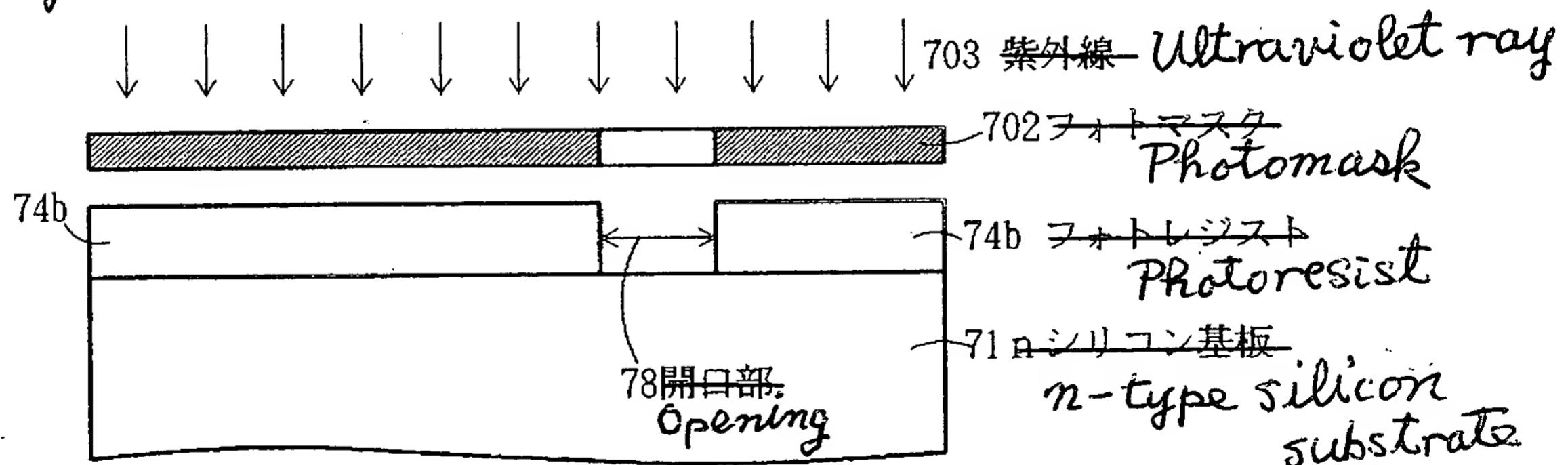


Fig. 6

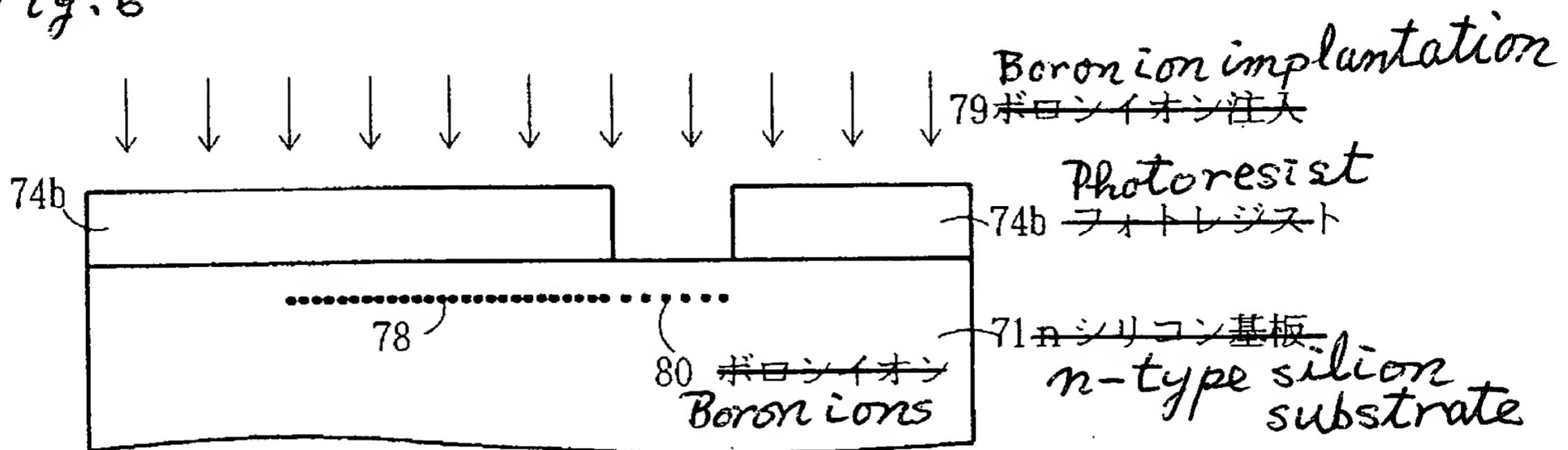


Fig. 7

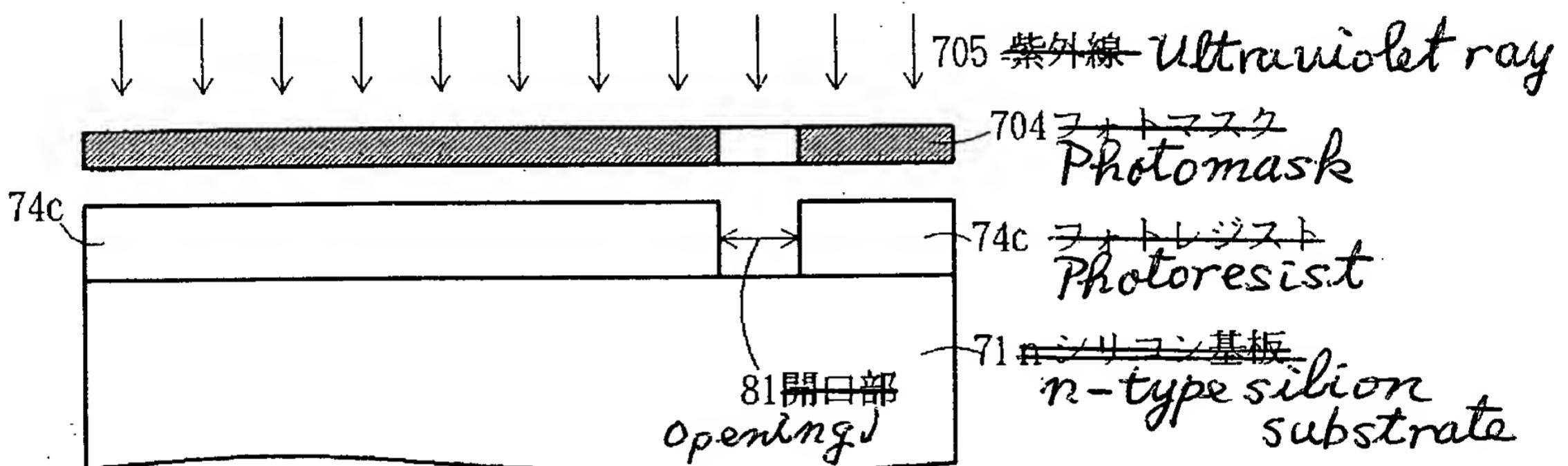


Fig. 8

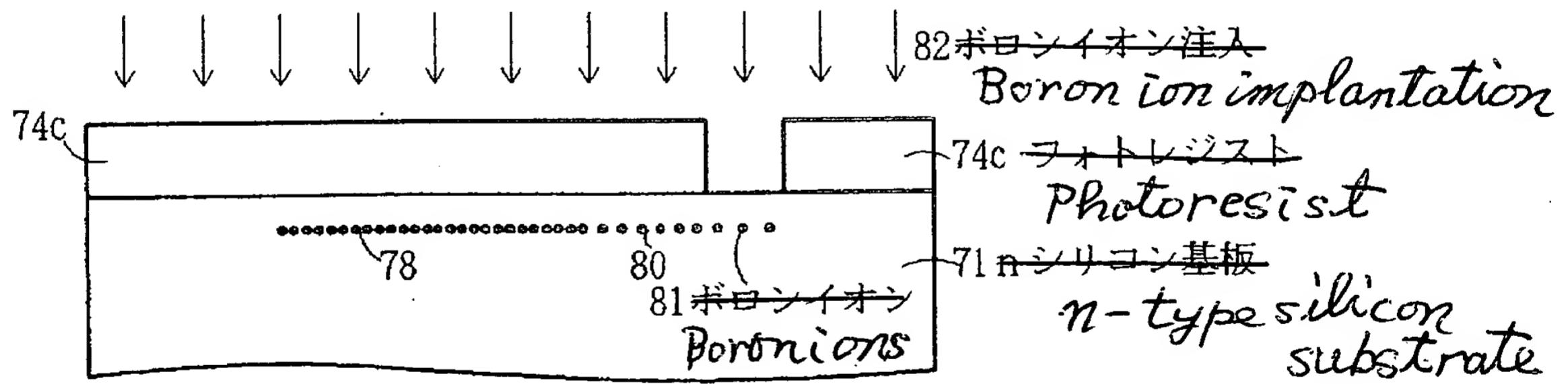


Fig. 9

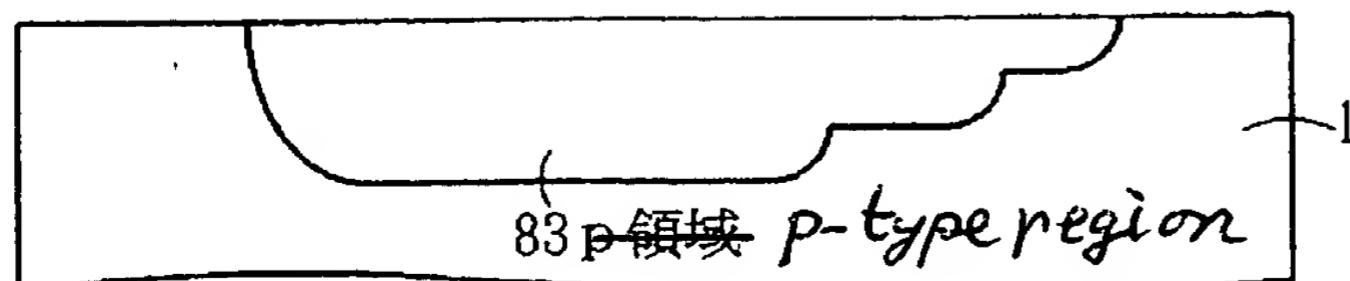


Fig. 10

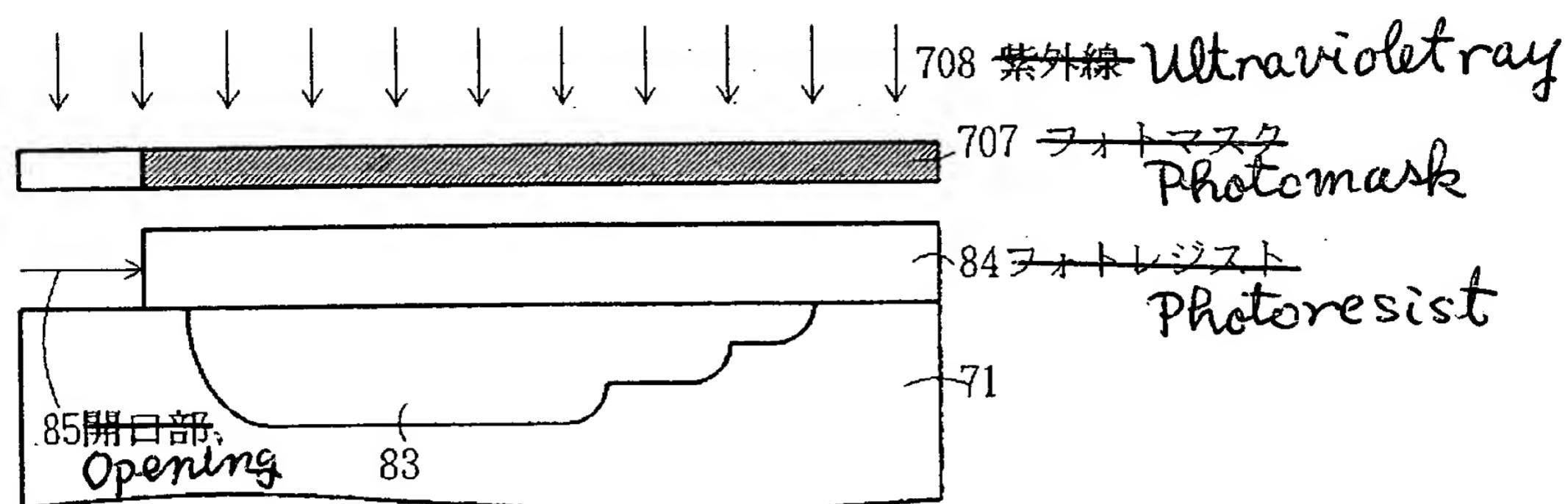


Fig 11

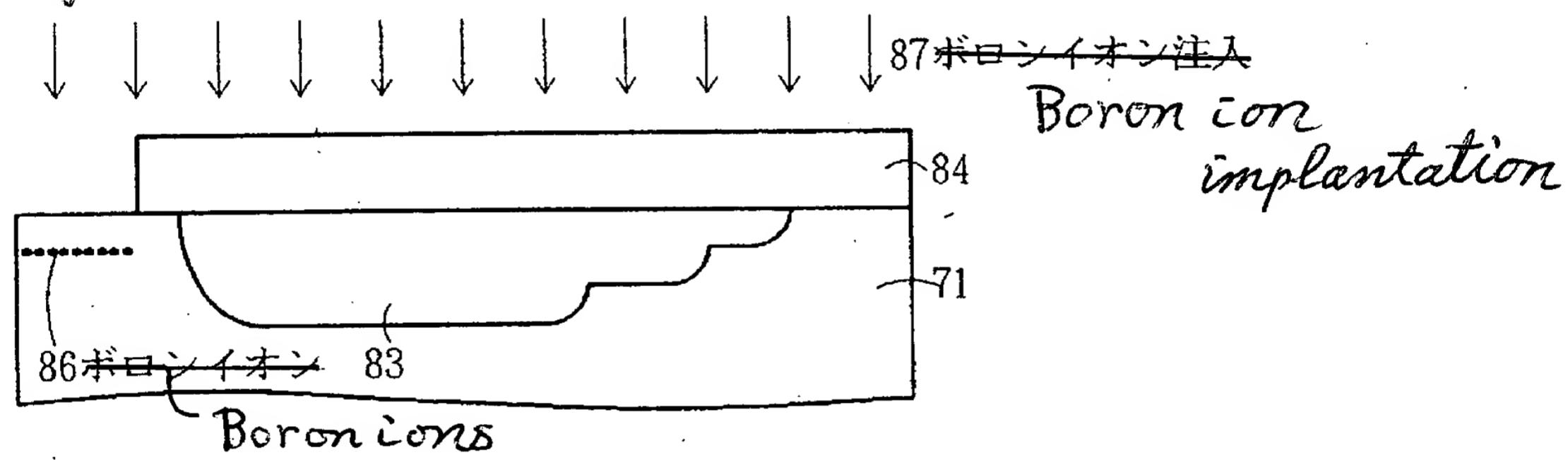


Fig. 12

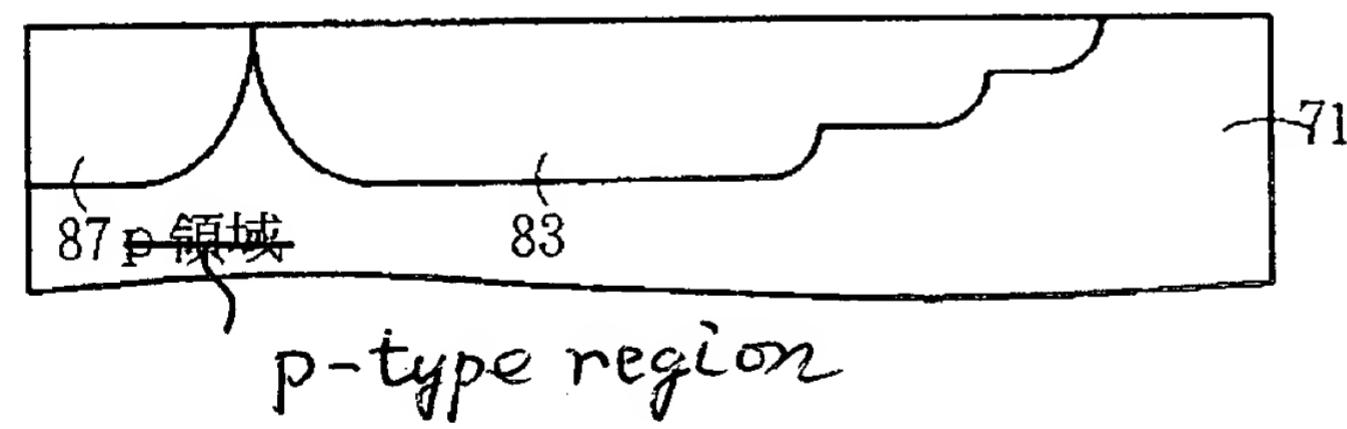
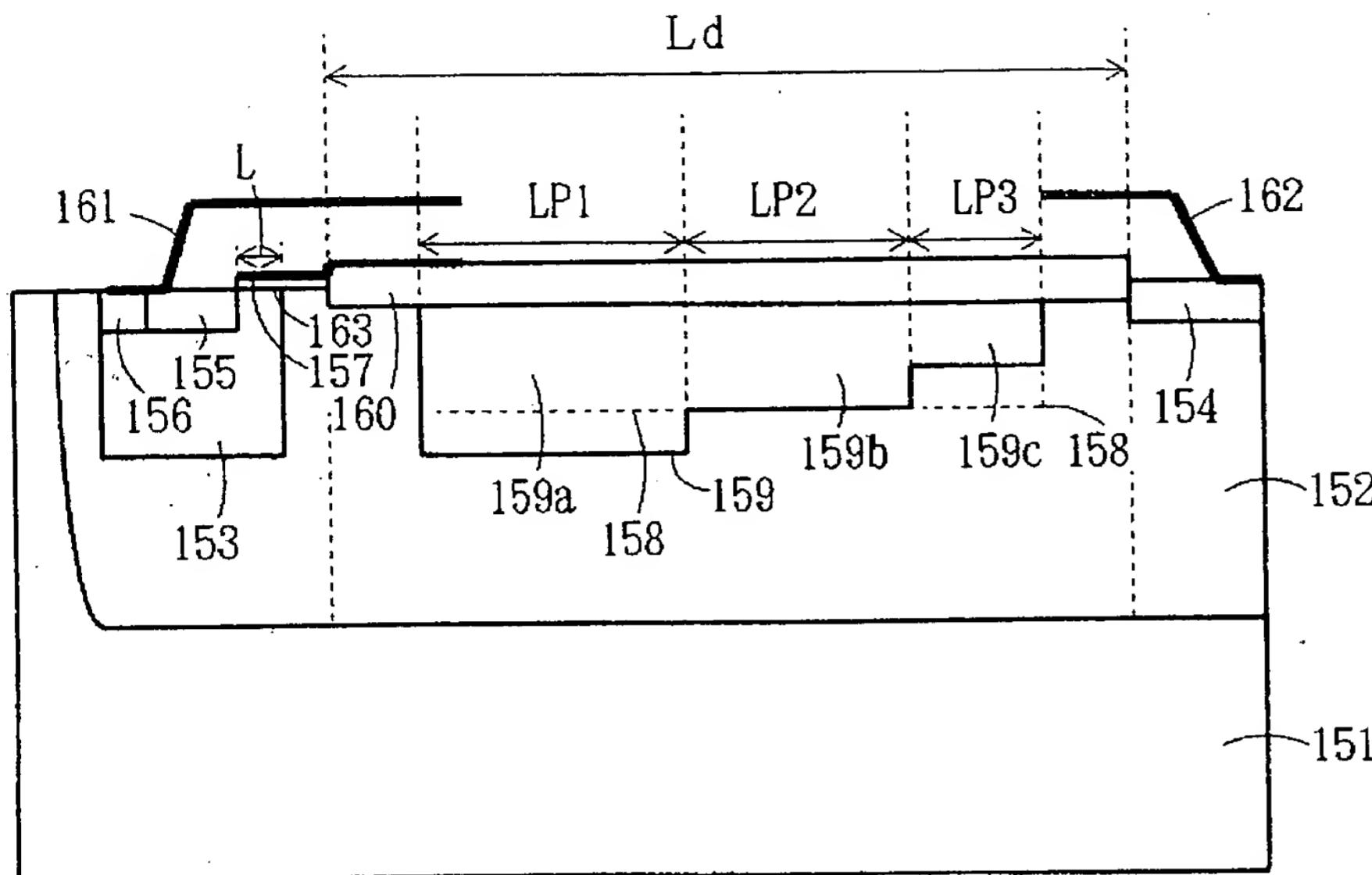


Fig. 13



- 151: p-type substrate
- 152: n-type well region
- 153: p-type base region
- 154: n-type drain region
- 155: n-type source region
- 156: p⁺-type contact region
- 157: Gate electrode
- 158: Boron diffusion depth
- 159: p-type diffusion region (p-type offset region)
- 159a: First p-type sub-region
- 159b: Second p-type sub-region
- 159c: Third p-type sub-region
- 160: Insulation film
- 161: Source electrode
- 162: Drain electrode
- 163: Gate insulation film

Fig. 14

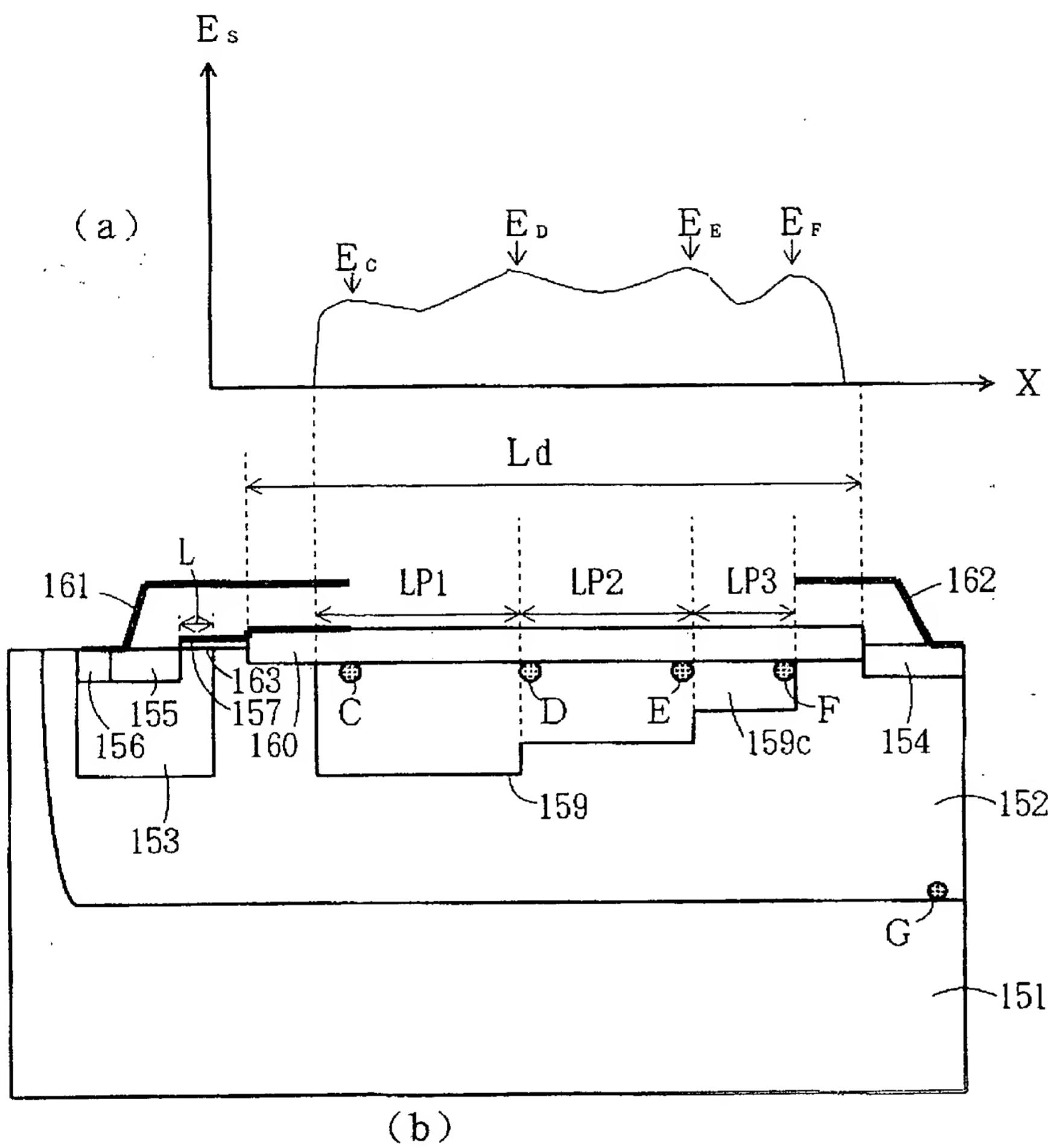
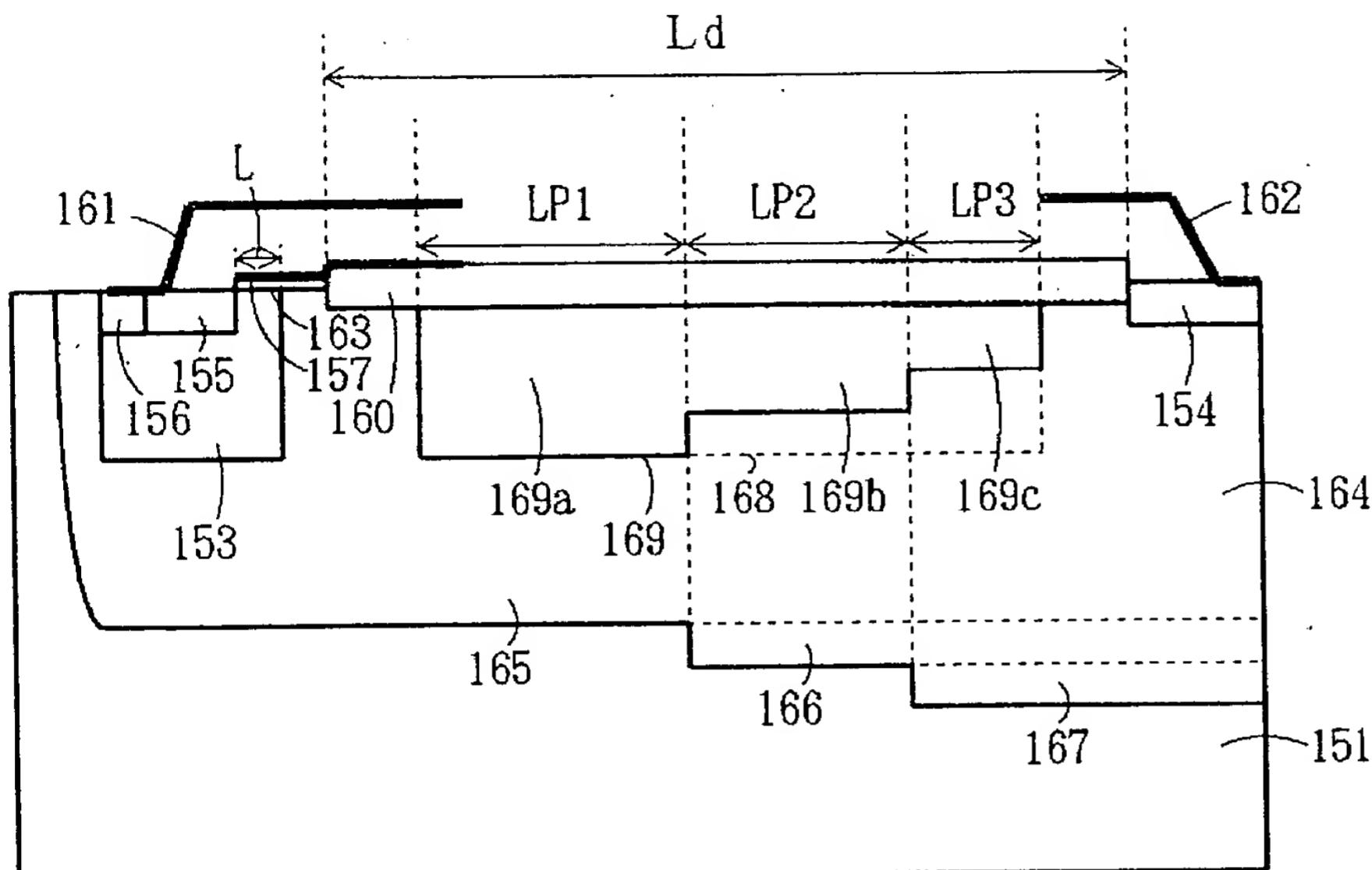


Fig. 15



- 164: n-type well region
- 165: First well sub-region
- 166: Second well sub-region
- 167: Third well sub-region
- 168: Boron diffusion depth
- 169: p-type diffusion region
- 169a: First p-type sub-region
- 169b: Second p-type sub-region
- 169c: Third p-type sub-region

Fig. 16(a)

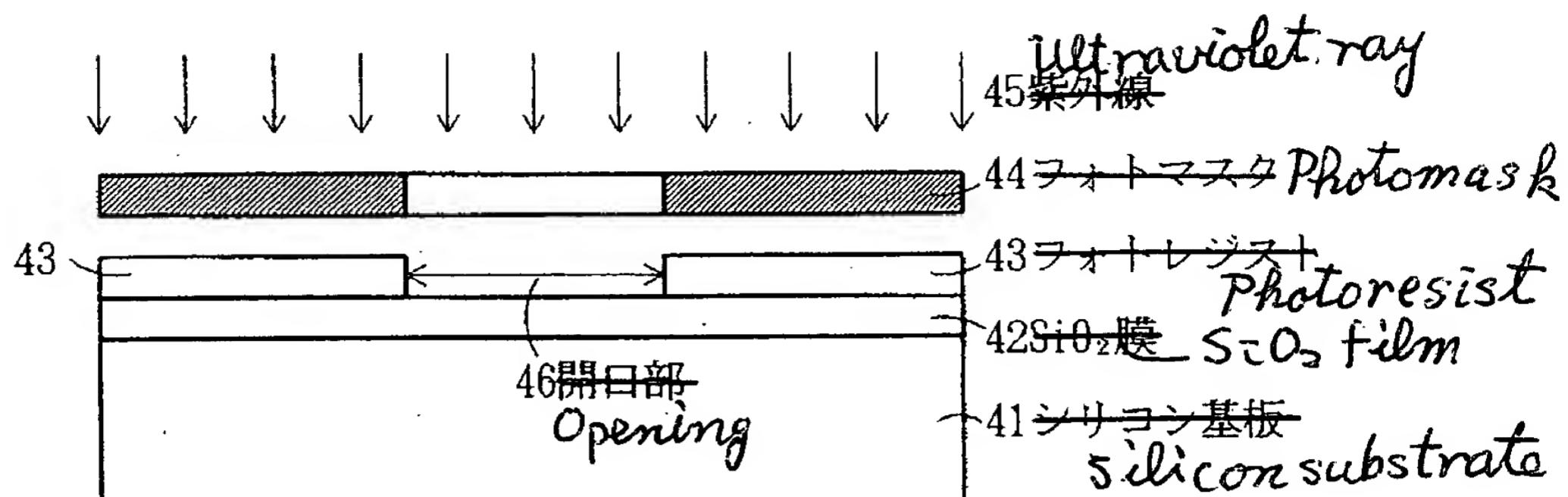


Fig. 16(b)

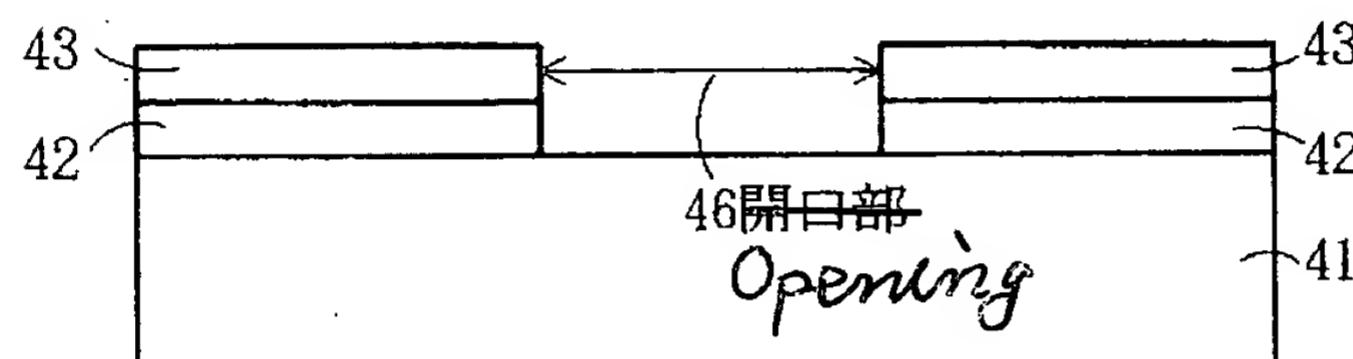


Fig. 16(c)

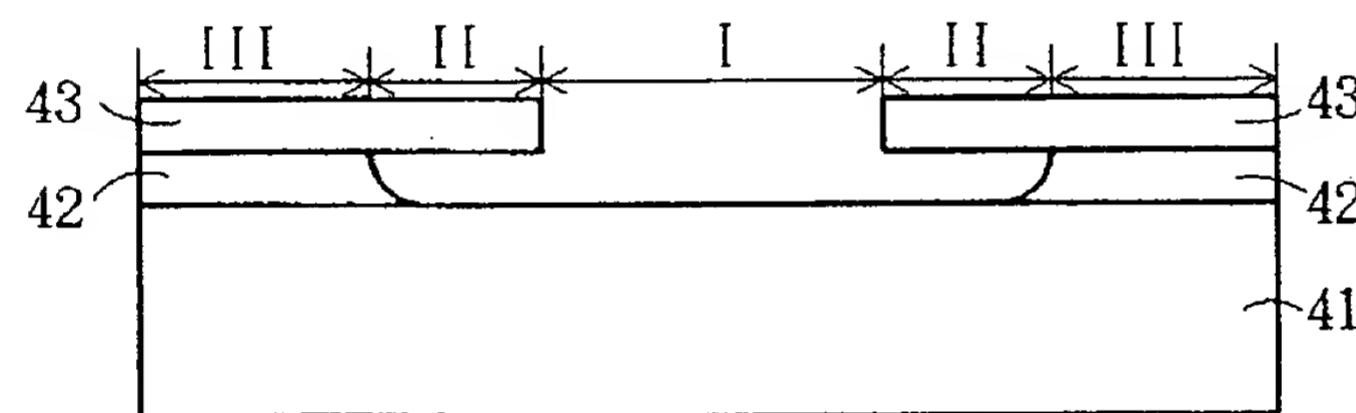


Fig. 16(d)

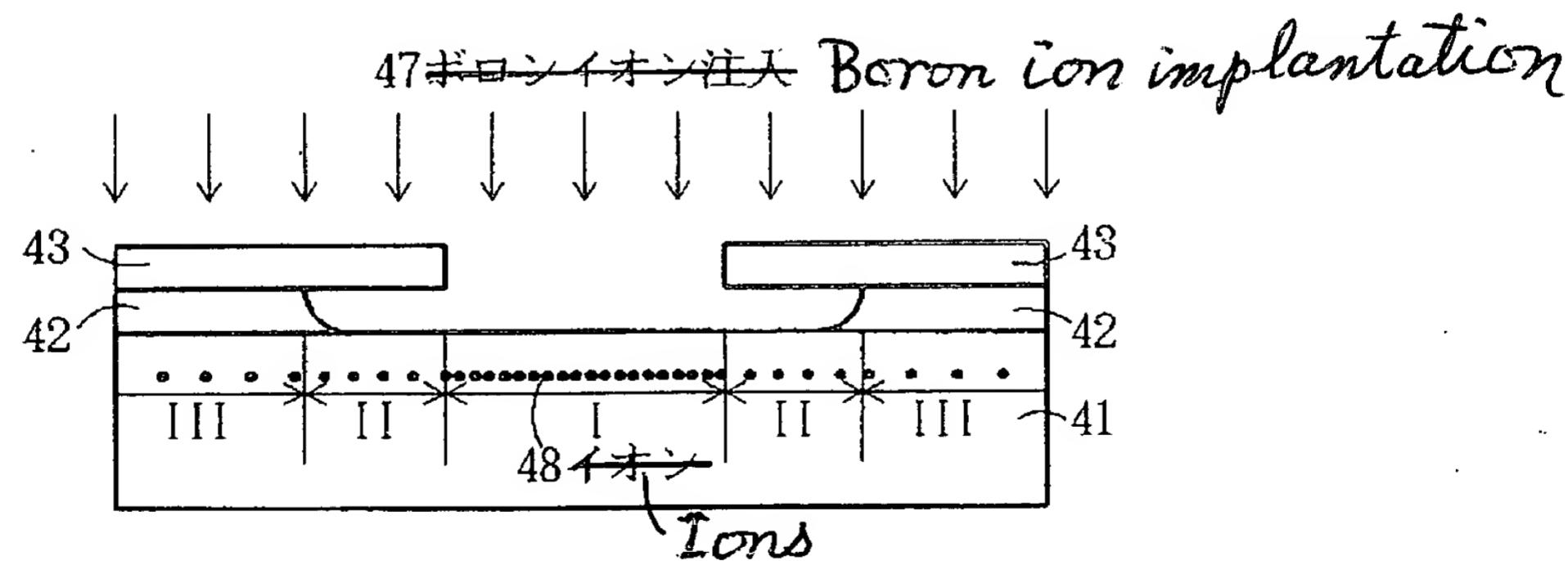
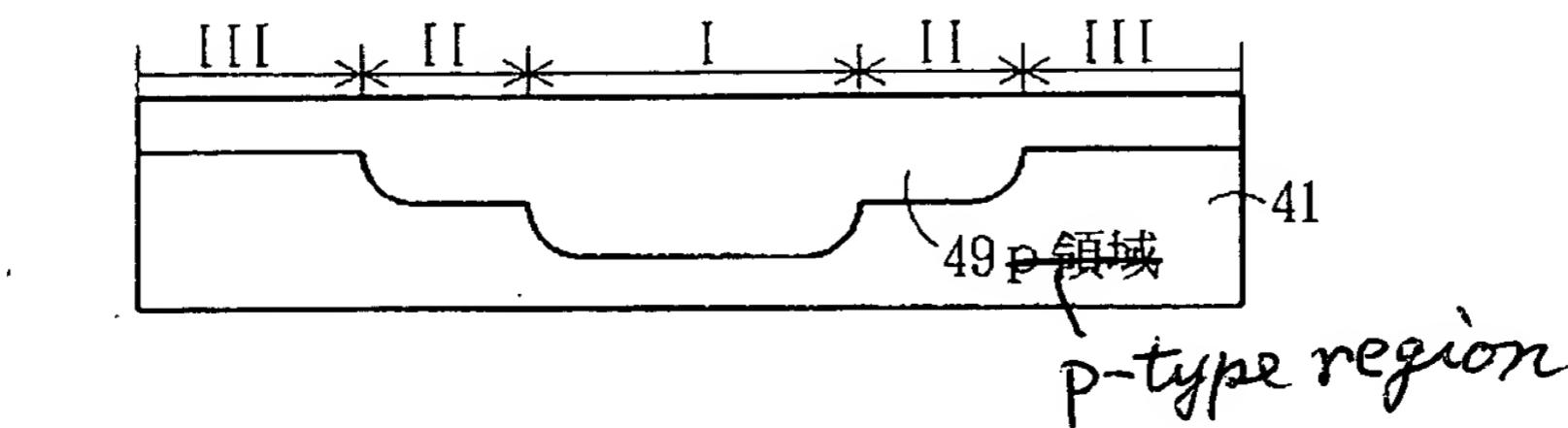


Fig. 16(e)



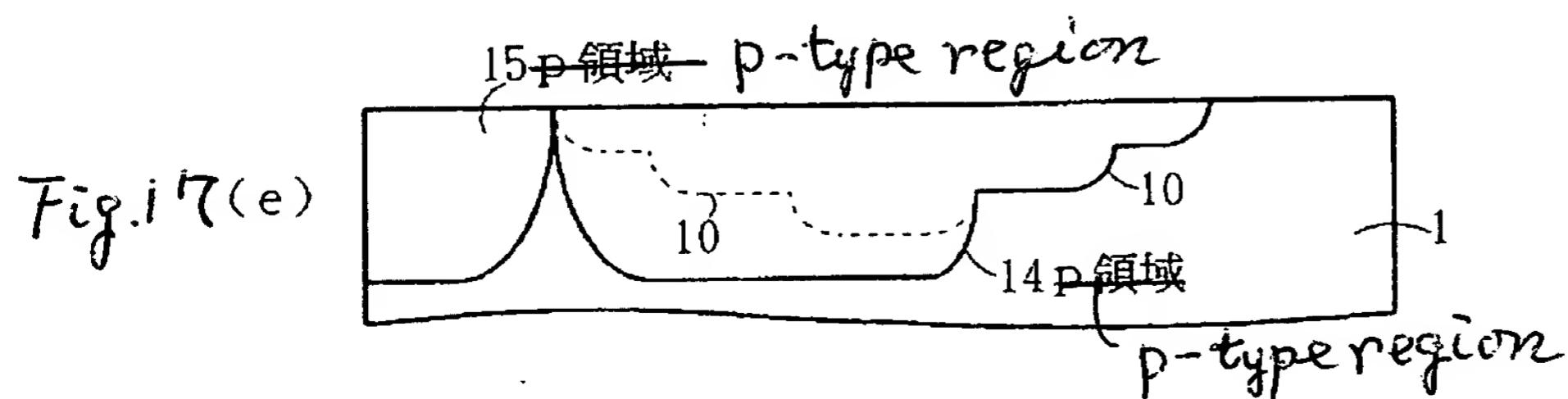
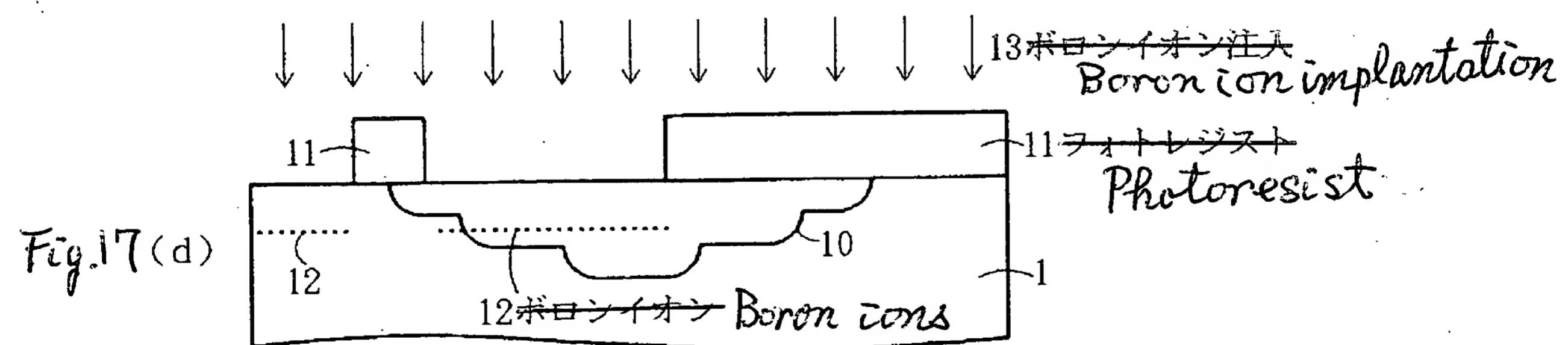
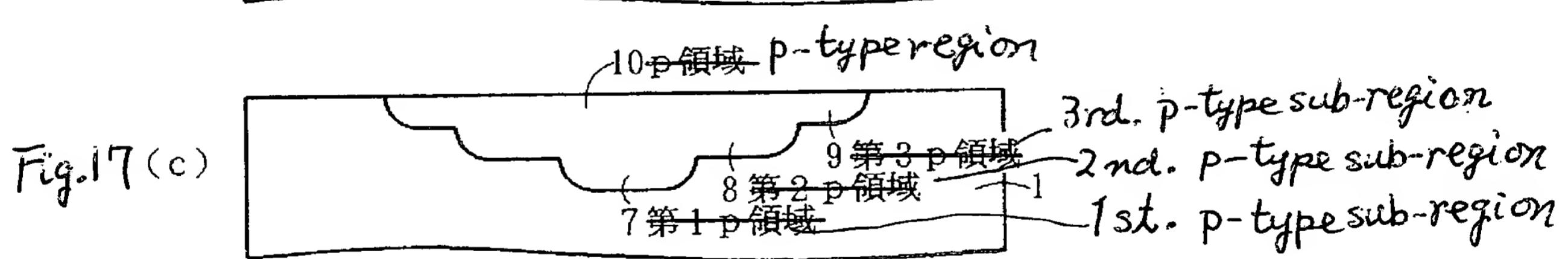
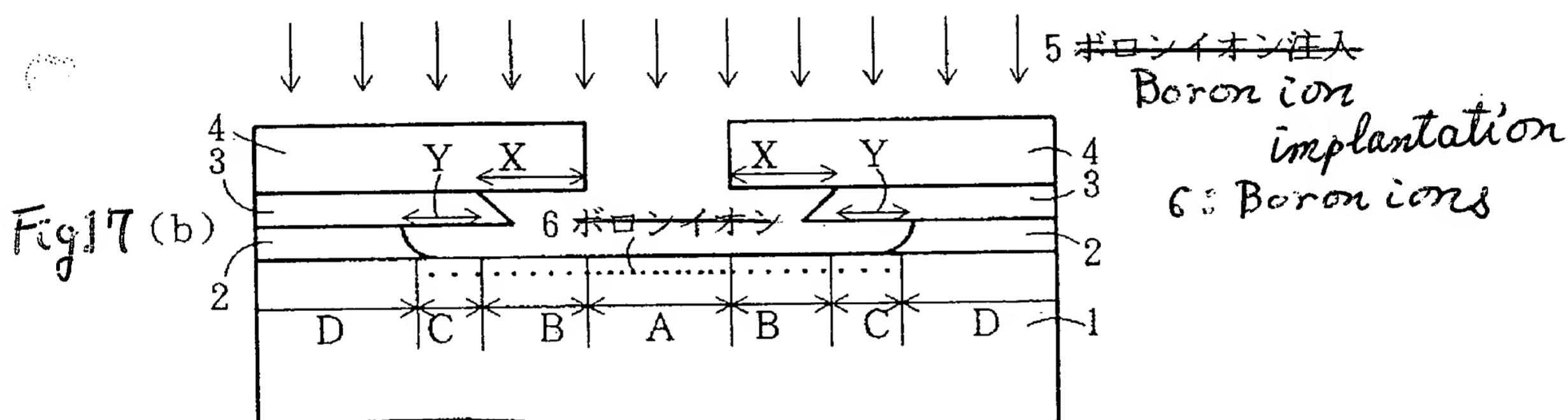
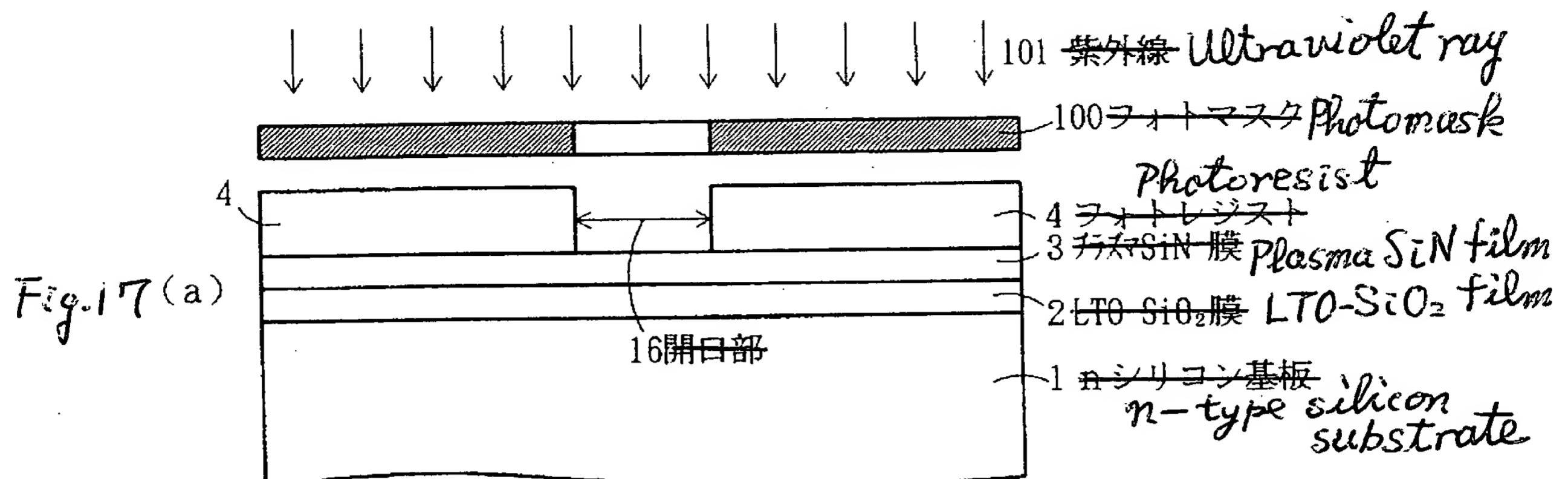


Fig. 18(a)

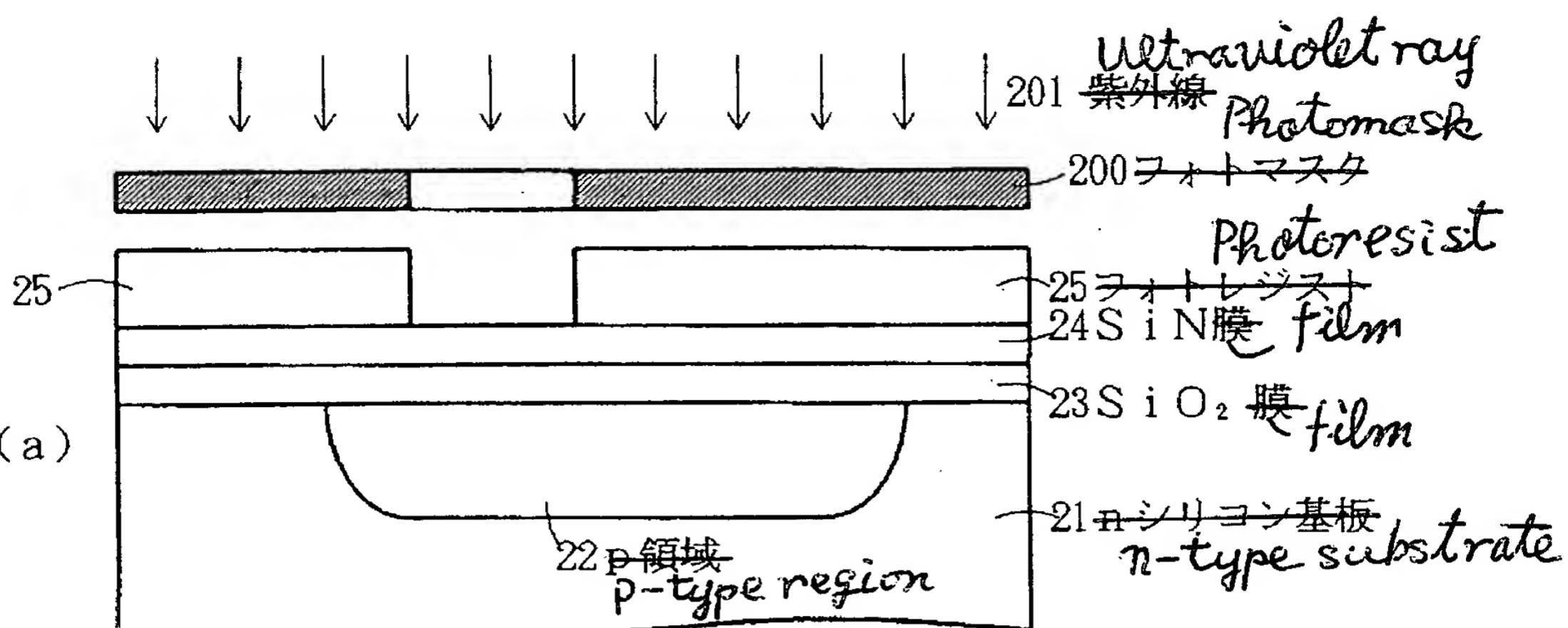


Fig. 18(b)

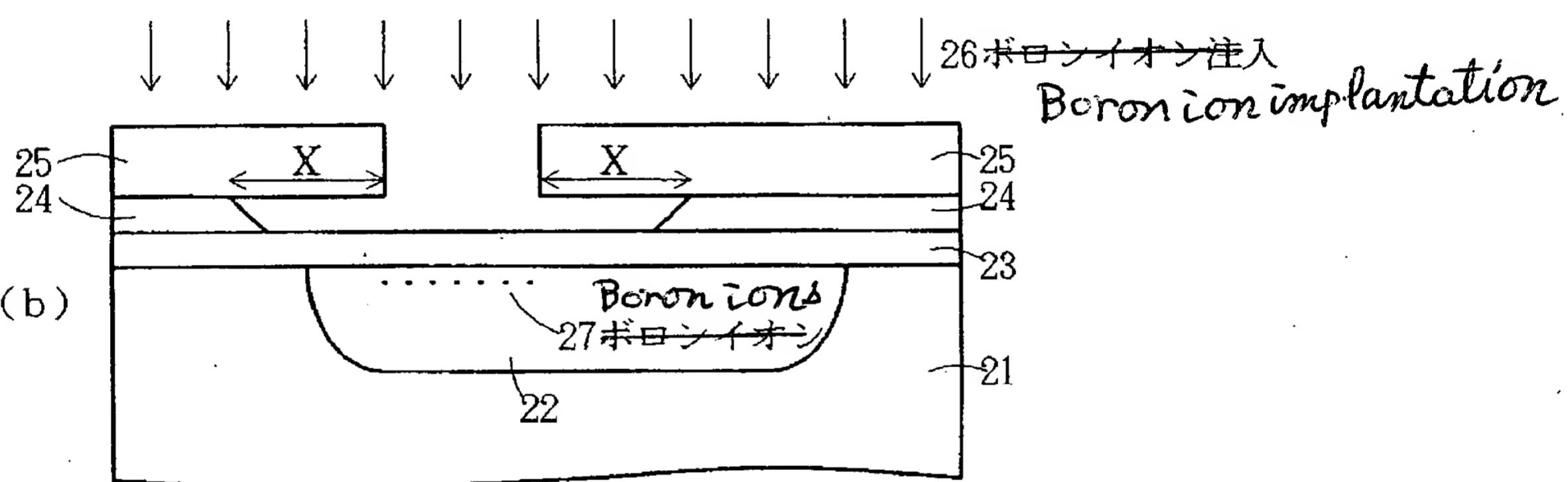


Fig. 18(c)

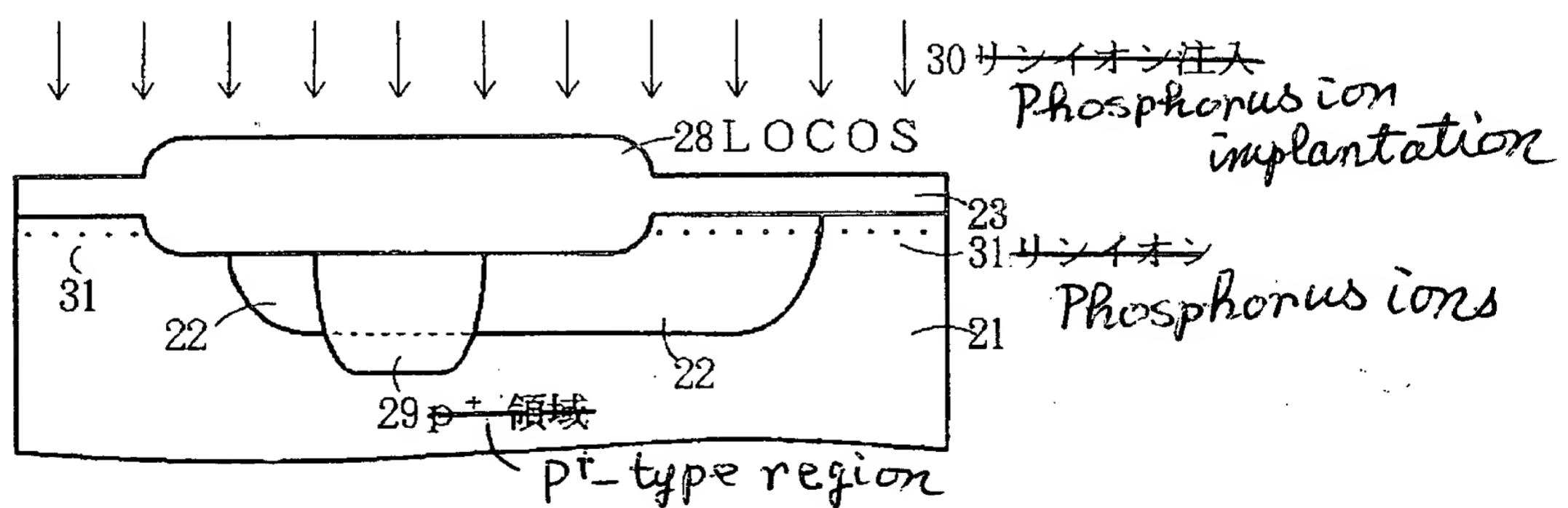


Fig. 18(d)

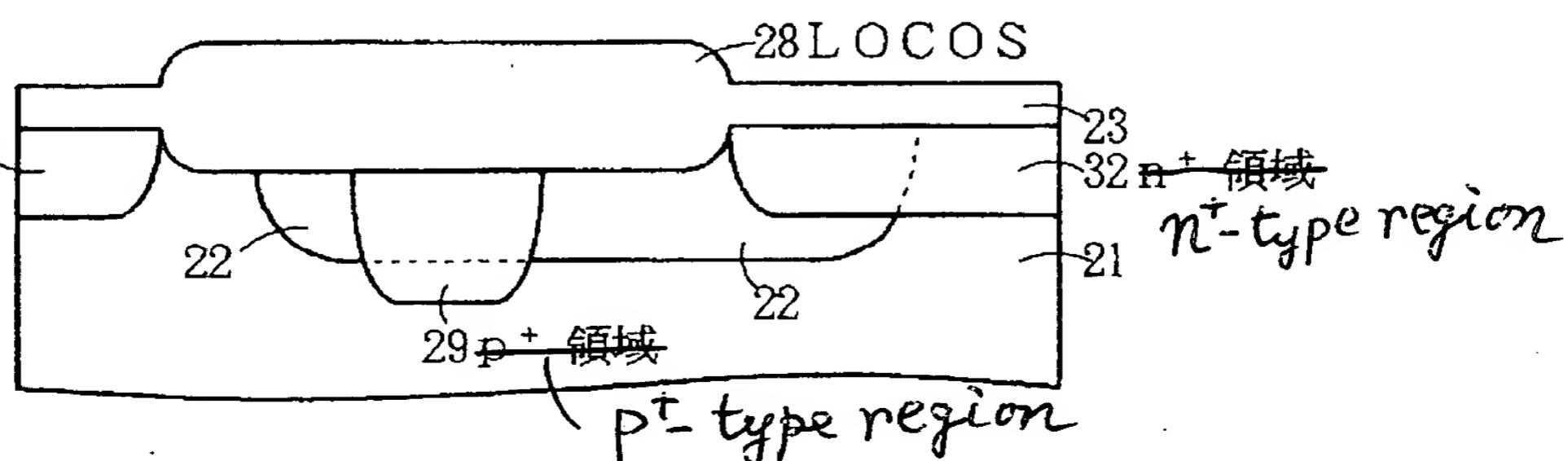


Fig. 19

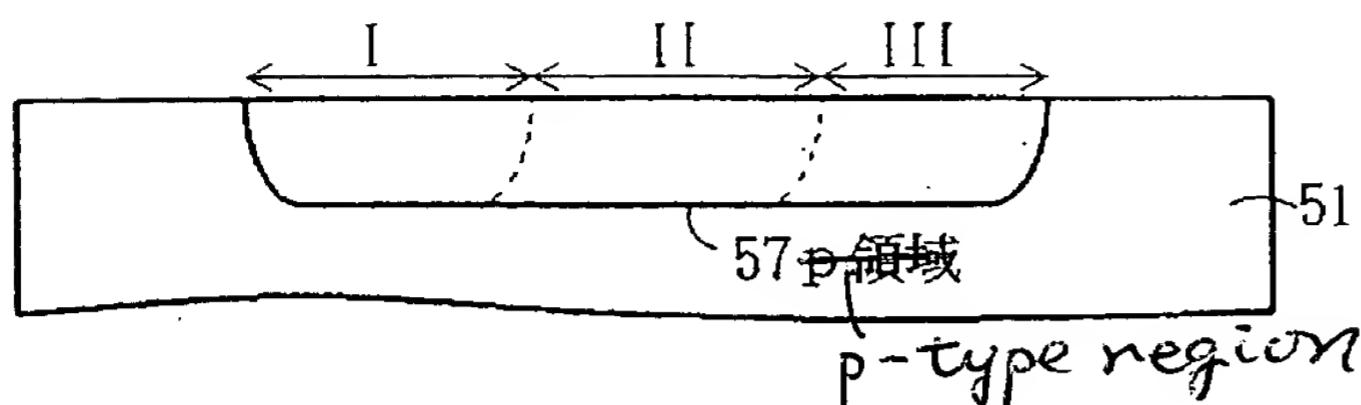
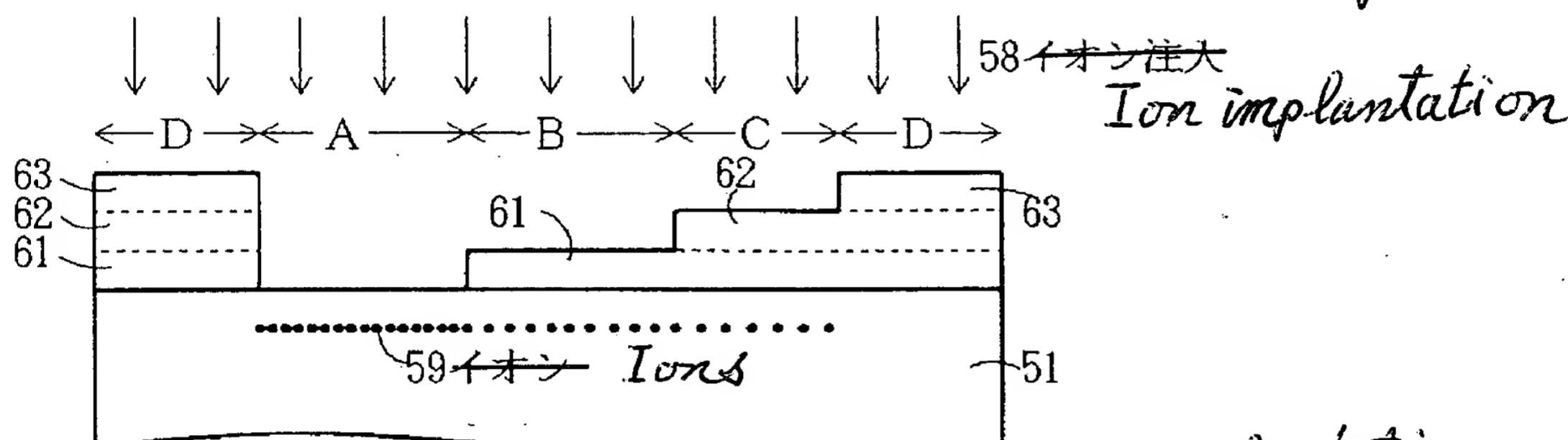
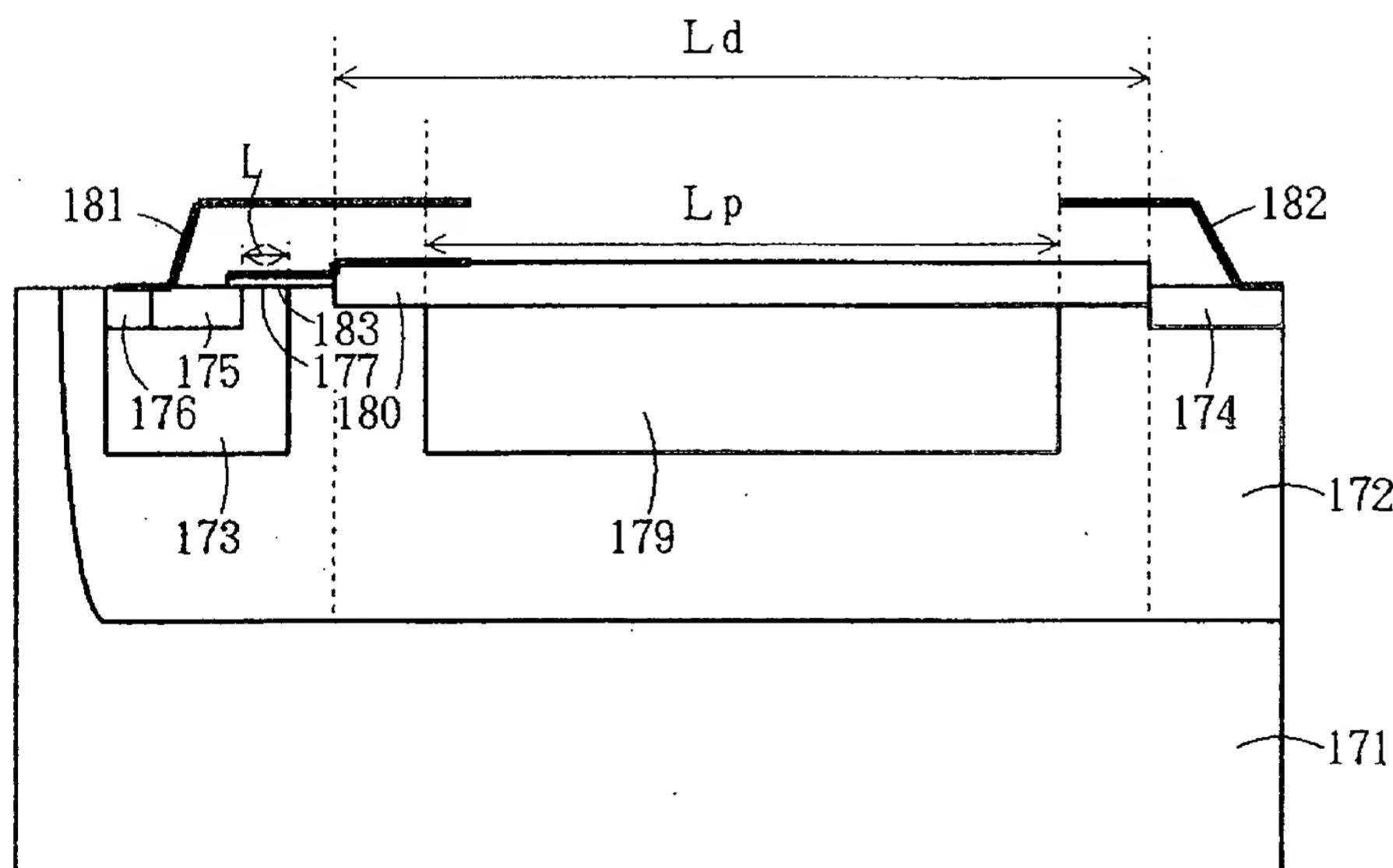


Fig. 20



61, 62, 63 . . . イオン注入マスク mask for ion implantation

Fig. 21



171: p-type substrate

172: n-type well region

173: p-type base region

174: n-type drain region

175: n-type source region

176: p⁺-type contact region

177: Gate electrode

179: p-type diffusion region (p-type offset region)

180: Insulation film

181: Source electrode

182: Drain electrode

183: Gate oxide film

Fig. 22(a)

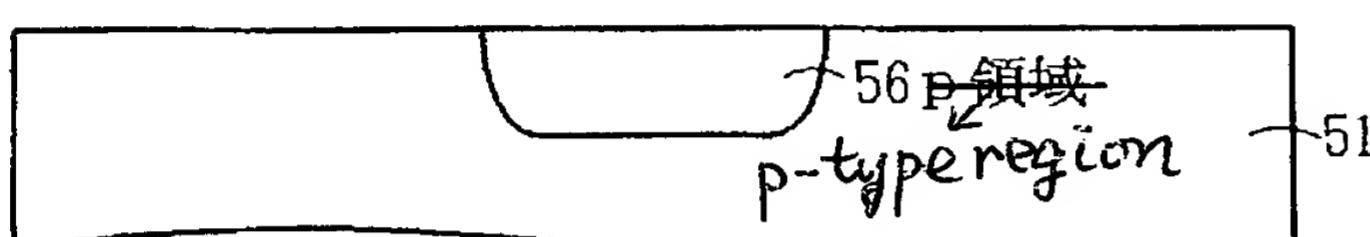
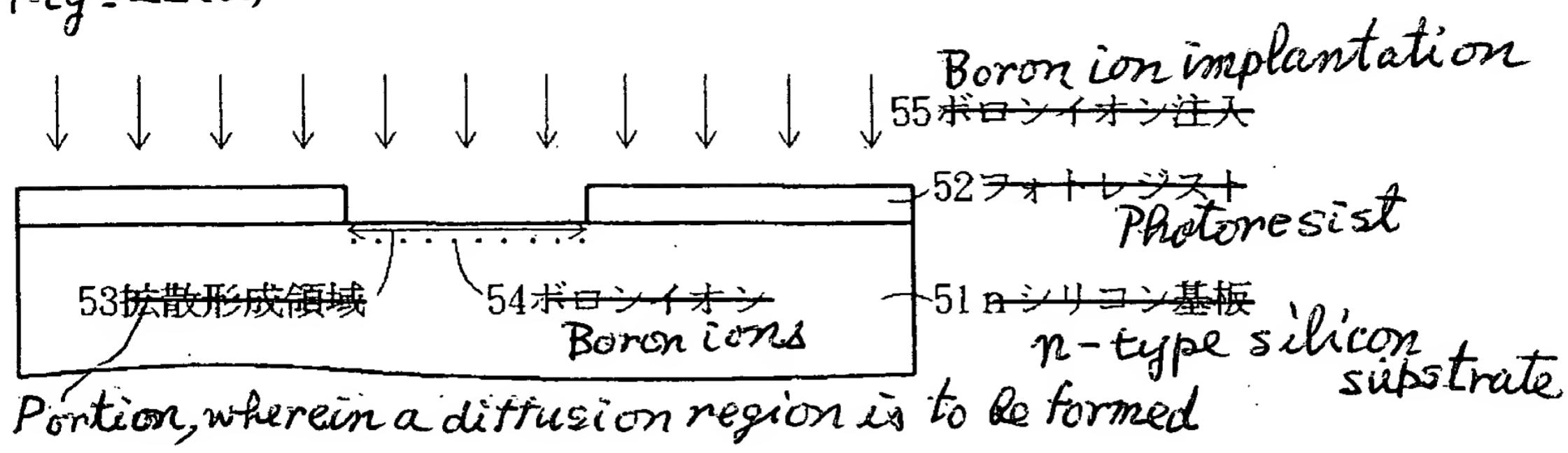


Fig. 22(b)

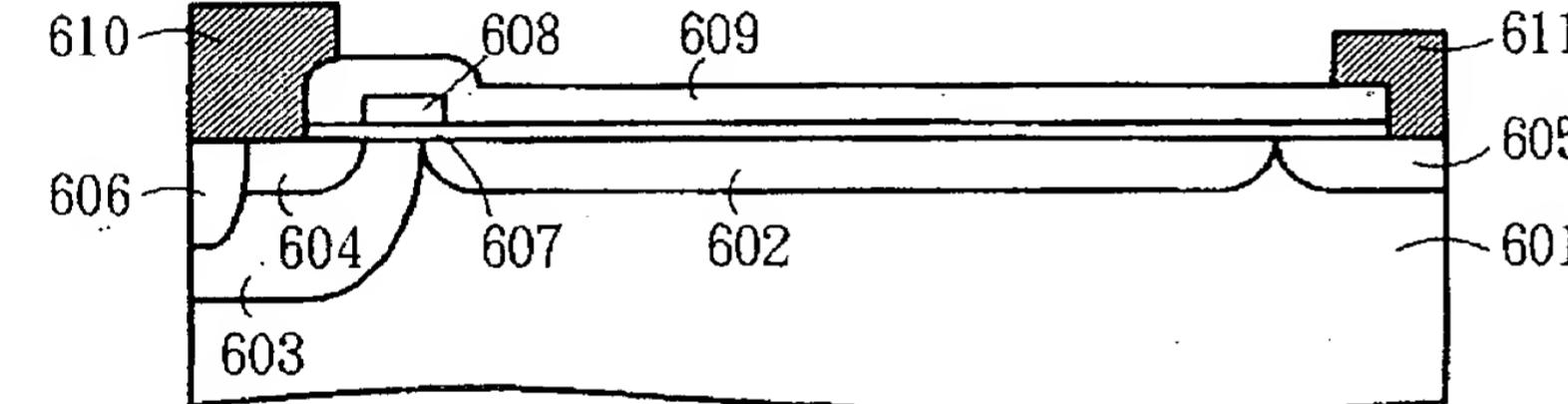


Fig. 23

- | | |
|---|-----------------------|
| 601: n-type silicon substrate | 607: Gate oxide film |
| 602: p-type region (p-type offset region) | 608: Gate electrode |
| 603: p-type region (p-type base region) | 609: Insulation film |
| 604: n-type source region | 610: Source electrode |
| 605: n-type drain region | 611: Drain electrode |
| 606: p-type contact region | |

Fig. 24

